

BTA2008-600D

3Q Hi-Com Triac Rev.03 - 09 March 2022

Product data sheet

1. General description

Planar passivated high commutation three quadrant triac in a TO92 plastic package. This "series D" triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers and logic ICs including microcontrollers.

2. Features and benefits

- 3Q technology for improved noise immunity
- Direct gate triggering from low power drivers and logic ICs
- · High commutation capability with very sensitive gate
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- Very sensitive gate for easy logic level triggering

3. Applications

- · Low power motor controls
- Small inductive loads e.g. solenoids, door locks, water valves
- · Small loads in large white goods

4. Quick reference data

able 1. Q	uick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Absolute	maximum rating		, , , , , , , , , , , , , , , , , , ,			
V_{DRM}	repetitive peak off- state voltage		-	-	600	V
$I_{T(RMS)}$	RMS on-state current	square-wave pulse; T _{lead} ≤ 70 °C; <u>Fig. 1; Fig. 2</u> ; <u>Fig. 3</u>	-	-	0.8	A
I _{TSM}	non-repetitive peak forward current	full sine wave; t_p = 20 ms; $T_{j(init)}$ = 25 °C; Fig. 4; Fig. 5	-	-	9	A
		full sine wave; t_p = 16.7 ms; $T_{j(init)}$ = 25 °C	-	-	9.9	А
Tj	junction temperature		-	-	125	°C
Static ch	aracteristics					
I _{GT} gate trigger current	gate trigger current	$V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2+ G+} $ T _j = 25 °C; Fig. 7	0.25	-	5	mA
		$V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2+ G-}$ T _j = 25 °C; Fig. 7	0.25	-	5	mA
		V _D = 12 V; I _T = 0.1 A; T2- G- T _i = 25 °C; <u>Fig. 7</u>	0.25	-	5	mA

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	10	mA
V _T	on-state voltage	I _T = 0.85 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.35	1.6	V
Dynamic	characteristics					
dV _D /dt	rate of rise of off-state voltage	$\label{eq:V_DM} \begin{array}{l} V_{\text{DM}} = 402 \; \text{V}; \; T_{j} = 125 \; ^{\circ}\text{C}; \; \text{R}_{\text{GT1}} = 220 \; \Omega; \\ (V_{\text{DM}} = 67\% \; \text{of} \; V_{\text{DRM}}); \; \text{exponential} \\ \text{waveform} \end{array}$	200	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; \text{ T}_j = 125 \text{ °C}; \text{ I}_{T(RMS)} = 0.8 \text{ A}; $ $dV_{com}/dt = 10 \text{ V}/\mu\text{s}; \text{ gate open circuit}; $	0.5	-	-	A/ms

5. Pinning information

Table 2. Pinning information								
Pin	Symbol	Description	Simplified outline	Graphic symbol				
1	T2	main terminal 2		NI				
2	G	gate	l Linn I					
3	Τ1	main terminal 1	() () () 3 2 1 TO-92 (SOT54)	G sym051				

6. Ordering information

Table 3. Ordering information								
Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date		
BTA2008-600D	TO92	BTA2008-600D,412	Bulk	1000	SOT54	14-Nov-2013		

7. Marking

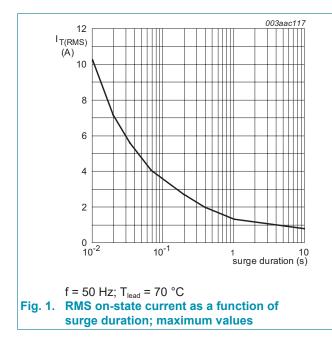
Table 4. Marking codes	
Type number	Marking codes
BTA2008-600D	2008-6D

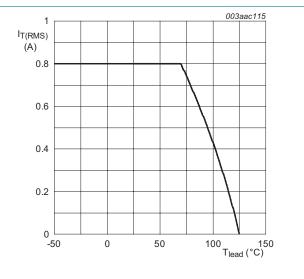
8. Limiting values

Table 5. Limiting values

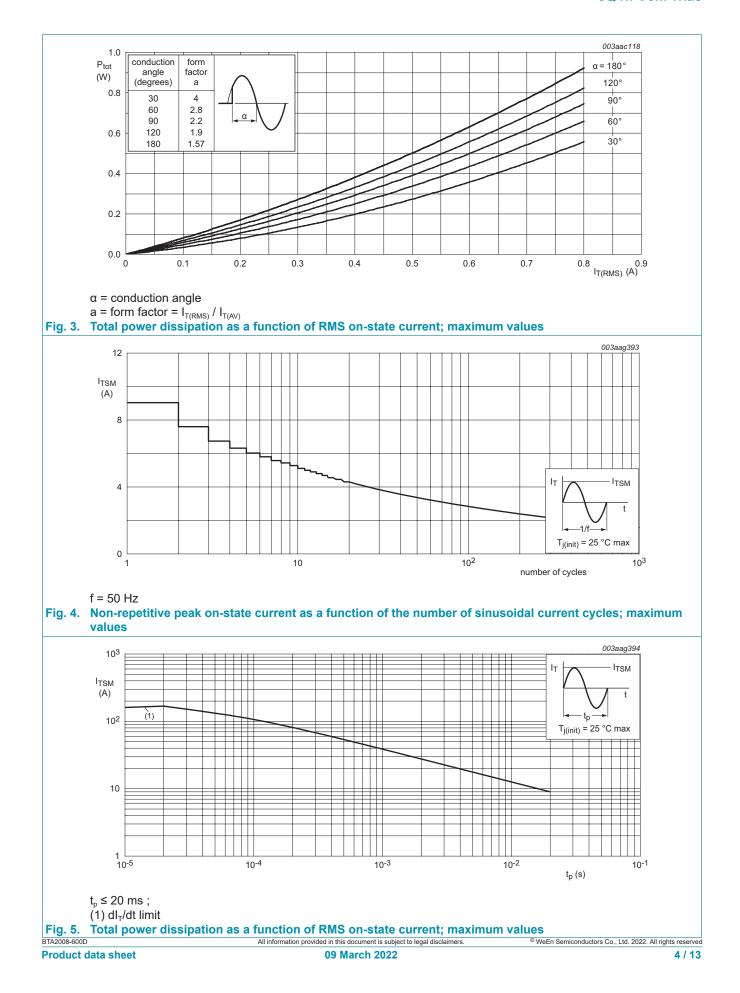
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{lead} ≤ 70°C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	0.8	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; t _p = 20 ms; T _{j(init)} = 25 °C; <u>Fig. 4; Fig. 5</u>	-	9	A
		full sine wave; t_p = 16.7 ms; $T_{j(init)}$ = 25 °C	-	9.9	А
l ² t	l ² t for fusing	t _p = 10 ms; sine wave	-	0.41	A²/s
dl _T /dt	rate of rise of on-state current	I _G = 10 mA	-	100	A/µs
I _{GM}	peak gate current		-	1	А
P _{GM}	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C



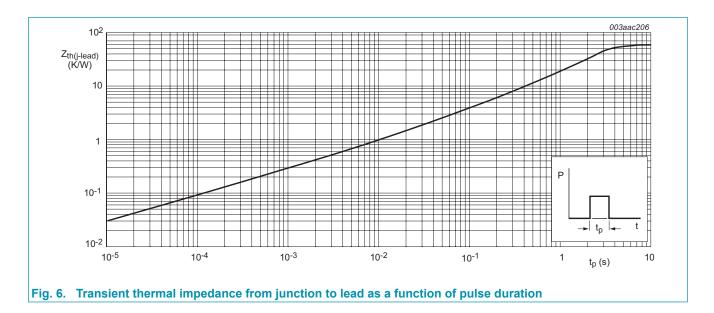






9. Thermal characteristics

Table 6. Th	ermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-lead)}}$	thermal resistance from junction to lead	full cycle; <u>Fig. 6</u>	-	-	60	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	printed circuit board mounted: lead length = 4 mm	-	150	-	K/W

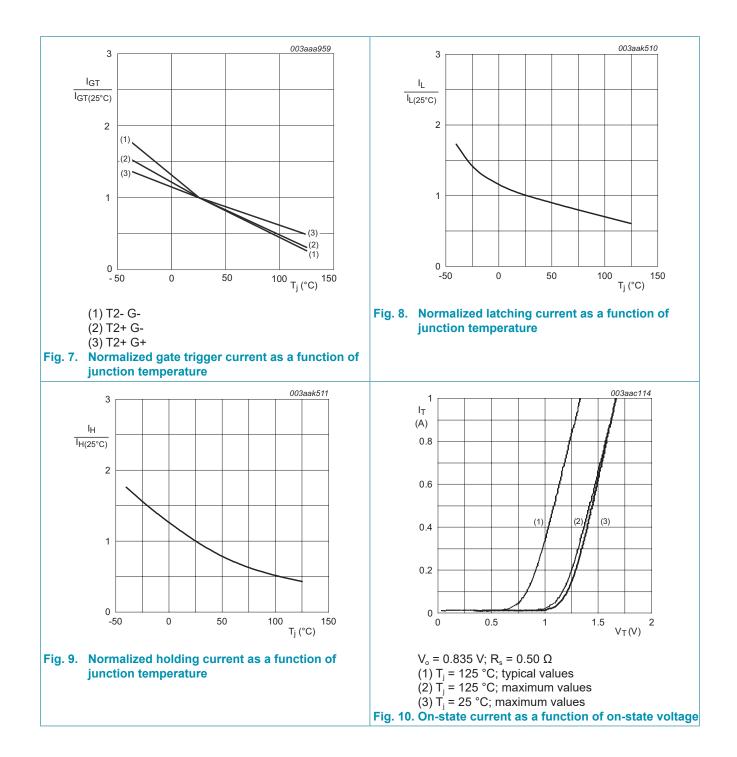


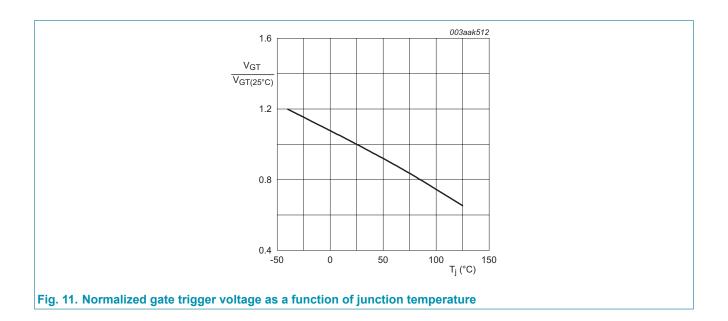
10. Characteristics

	aracteristics			_		
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	$V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2+ G+};$ $\text{T}_{j} = 25 \text{ °C}; \text{ Fig. 7}$	0.25	-	5	mA
		$V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2+ G-};$ $\text{T}_{j} = 25 \text{ °C}; \text{ Fig. 7}$	0.25	-	5	mA
		$V_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}; \text{ T2- G-};$ $T_{j} = 25 \text{ °C}; \text{ Fig. 7}$	0.25	-	5	mA
IL	latching current	$V_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}; \text{ T2+ G+};$ $T_{j} = 25 \text{ °C}; \text{ Fig. 8}$	-	-	10	mA
		$V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2+ G-};$ $\text{T}_{j} = 25 \text{ °C}; \text{ Fig. 8}$	-	-	20	mA
		$V_{D} = 12 \text{ V}; \text{ I}_{T} = 0.1 \text{ A}; \text{ T2- G-};$ $\text{T}_{j} = 25 \text{ °C}; \text{ Fig. 8}$	-	-	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 9</u>	-	-	10	mA
V _T	on-state voltage	I _T = 0.85 A; T _j = 25 °C; <u>Fig. 10</u>	-	1.35	1.6	V
V _{gt}	gate trigger voltage	$V_{D} = 12 \text{ V}; I_{T} = 0.1 \text{ A}; T_{j} = 25 \text{ °C};$ Fig. 11	-	0.9	1.5	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C	0.2	0.3	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic o	haracteristics	· · · · · · · · · · · · · · · · · · ·		I		
dV _D /dt	rate of rise of off-state voltage	$\label{eq:V_DM} \begin{array}{l} V_{DM} = 402 \; V; \; T_{j} = 125 \; ^{\circ}C; \; R_{GT1} = 220 \; \Omega; \\ (V_{DM} = 67\% \; of \; V_{DRM}); \; exponential \\ waveform \end{array}$	200	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	$V_D = 400 \text{ V}; \text{ T}_j = 125 \text{ °C}; \text{ I}_{T(RMS)} = 0.8 \text{ A}; dV_{com}/dt = 10 \text{ V}/\mu\text{s}; \text{ gate open circuit}$	0.5	-	-	A/ms

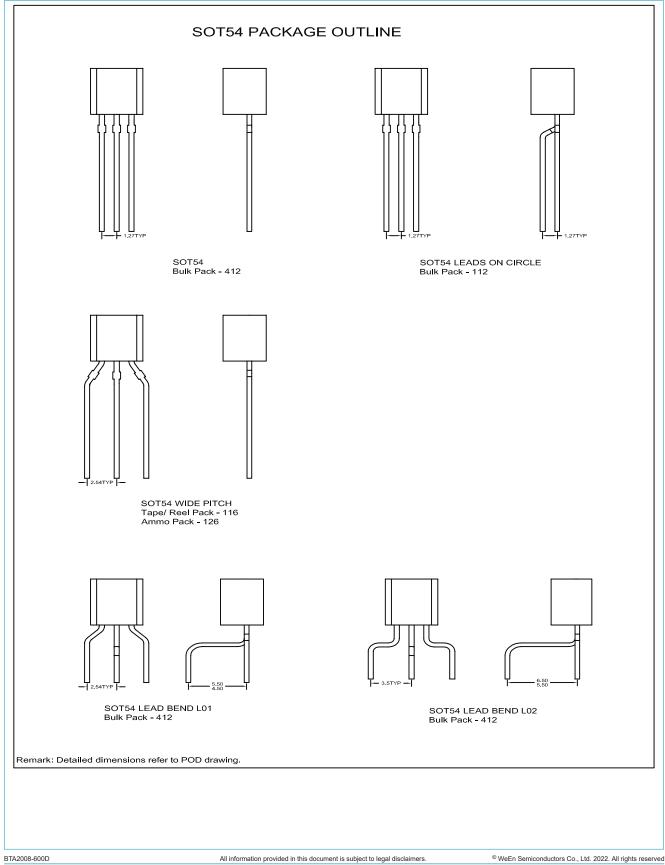
3Q Hi-Com Triac

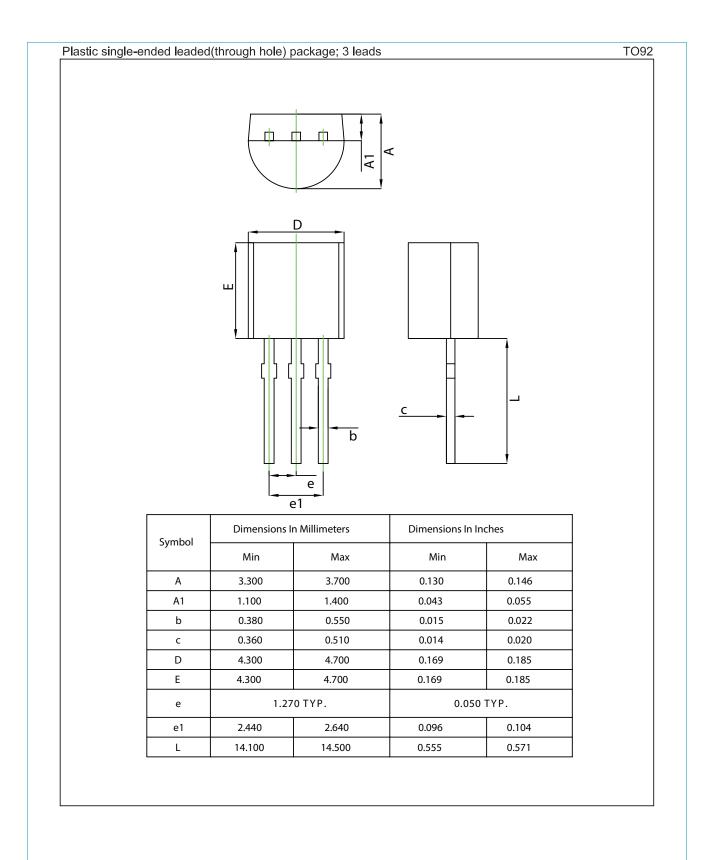
BTA2008-600D





11. Package outline





12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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For more information, please visit: http://www.ween-semi.com

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